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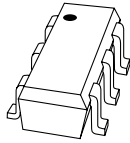
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Kind regards,

Team Nexperia



# PUM1/DG

50 V, 200 mA NPN general-purpose transistor/  
100 mA NPN resistor-equipped transistor

Rev. 01 — 14 July 2008

Product data sheet

## 1. Product profile

### 1.1 General description

NPN general-purpose transistor and NPN Resistor-Equipped Transistor (RET) in one SOT363 (SC-88) very small Surface-Mounted Device (SMD) plastic package.

### 1.2 Features

- General-purpose transistor:
  - ◆ 200 mA collector current  $I_C$
- Resistor-equipped transistor:
  - ◆ Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- Very small SMD plastic package
- AEC-Q101 qualified

### 1.3 Applications

- Inverter and switches
- Low-frequency amplifier
- Driver stages

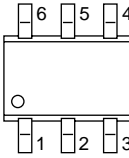
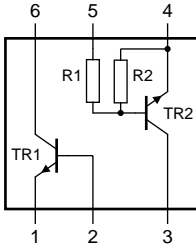
### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>TR1 (general-purpose transistor)</b>						
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
$I_C$	collector current		-	-	200	mA
$h_{FE}$	DC current gain	$V_{CE} = 10\text{ V};$ $I_C = 2\text{ mA}$	210	-	340	
<b>TR2 (resistor-equipped transistor)</b>						
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
$I_O$	output current		-	-	100	mA
R1	bias resistor 1 (input)		7	10	13	k $\Omega$
R2/R1	bias resistor ratio		0.8	1	1.2	

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1		
2	base TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	collector TR1		

006aab253

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PUML1/DG	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PUML1/DG	PA*

[1] \* = -: made in Hong Kong  
\* = p: made in Hong Kong  
\* = t: made in Malaysia  
\* = W: made in China

5. Limiting values

Table 5. Limiting values

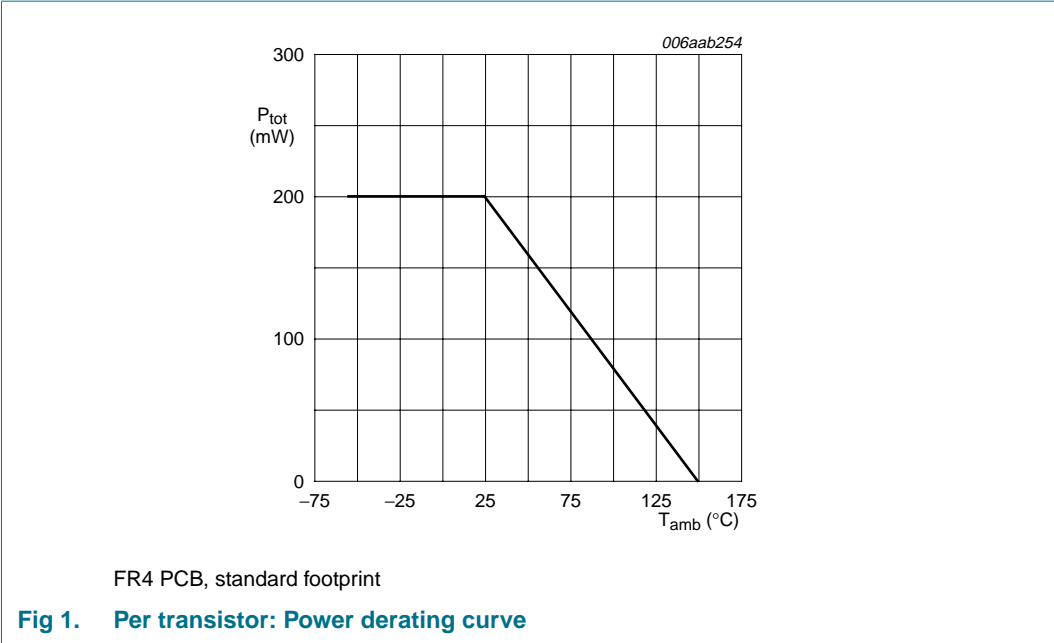
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
TR1 (general-purpose transistor)					
V <sub>CBO</sub>	collector-base voltage	open emitter	-	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	200	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	200	mA
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms	-	100	mA

**Table 5. Limiting values ...continued**  
*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	200	mW
<b>TR2 (resistor-equipped transistor)</b>					
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	10	V
V <sub>I</sub>	input voltage				
	positive		-	+40	V
	negative		-	-10	V
I <sub>O</sub>	output current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	200	mW
<b>Per device</b>					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	300	mW
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

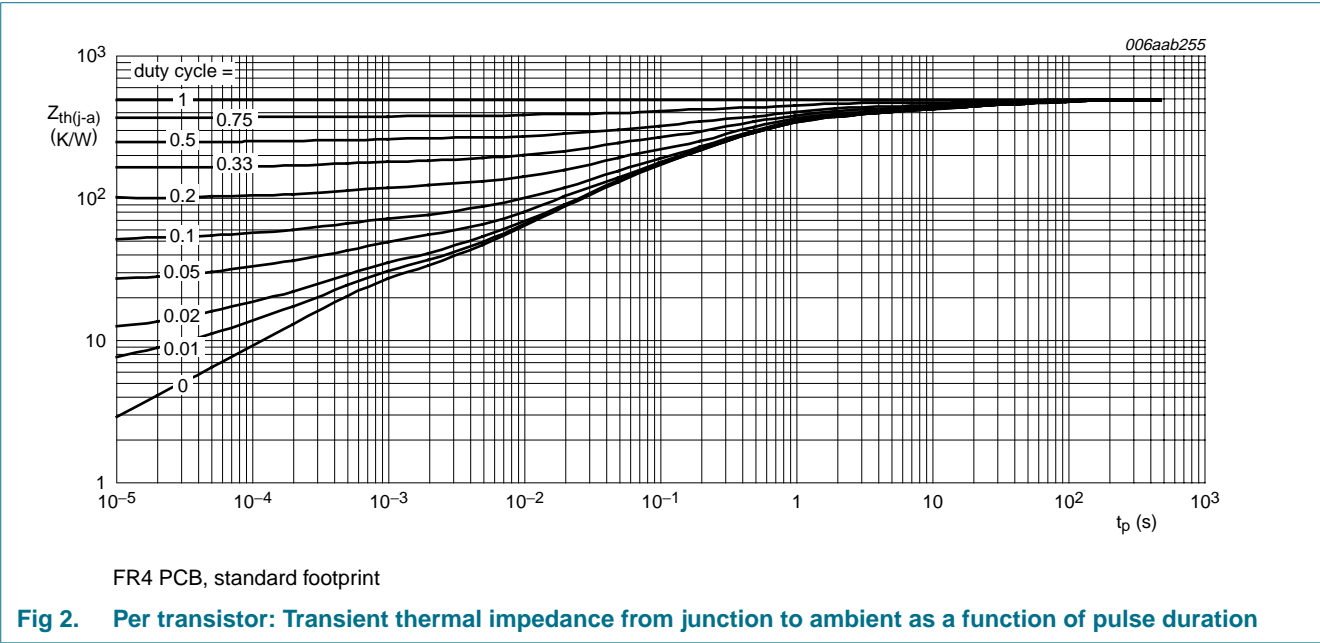


6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	625	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

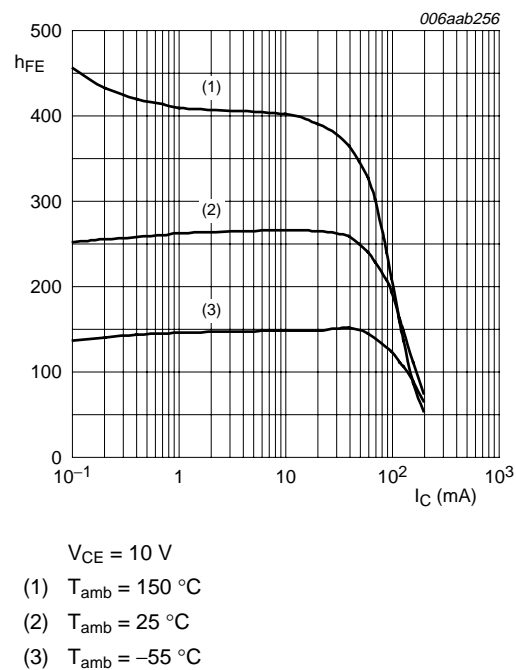


## 7. Characteristics

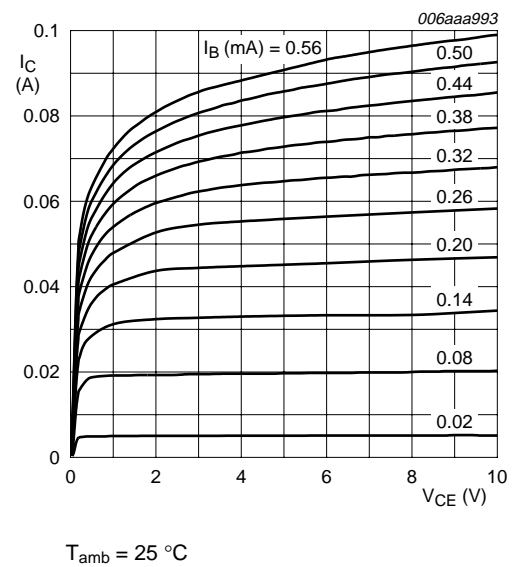
**Table 7. Characteristics**

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

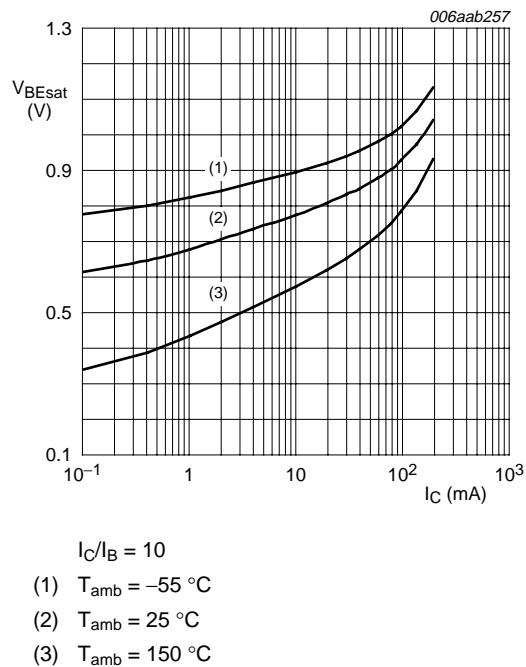
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>TR1 (general-purpose transistor)</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 60\text{ V}; I_E = 0\text{ A}$	-	-	10	nA
		$V_{CB} = 60\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	5	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	10	nA
$h_{FE}$	DC current gain	$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}$	90	-	-	
		$V_{CE} = 10\text{ V}; I_C = 2\text{ mA}$	210	-	340	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 10\text{ mA}$	-	-	250	mV
$f_T$	transition frequency	$V_{CE} = 10\text{ V}; I_C = 2\text{ mA}; f = 100\text{ MHz}$	100	-	-	MHz
		$V_{CE} = 6\text{ V}; I_C = 10\text{ mA}; f = 100\text{ MHz}$	-	230	-	MHz
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	-	-	3	pF
<b>TR2 (resistor-equipped transistor)</b>						
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 50\text{ V}; I_E = 0\text{ A}$	-	-	100	nA
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0\text{ A}$	-	-	1	$\mu\text{A}$
		$V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	50	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	400	$\mu\text{A}$
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 5\text{ mA}$	30	-	-	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5\text{ V}; I_C = 100\text{ }\mu\text{A}$	-	1.1	0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3\text{ V}; I_C = 10\text{ mA}$	2.5	1.8	-	V
R1	bias resistor 1 (input)		7	10	13	k $\Omega$
R2/R1	bias resistor ratio		0.8	1	1.2	
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = i_e = 0\text{ A}; f = 1\text{ MHz}$	-	-	2.5	pF



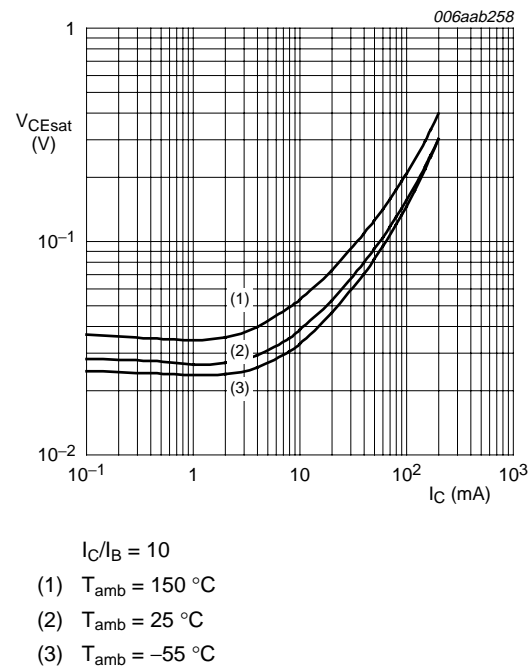
**Fig 3. TR1: DC current gain as a function of collector current; typical values**



**Fig 4. TR1: Collector current as a function of collector-emitter voltage; typical values**



**Fig 5. TR1: Base-emitter saturation voltage as a function of collector current; typical values**



**Fig 6. TR1: Collector-emitter saturation voltage as a function of collector current; typical values**

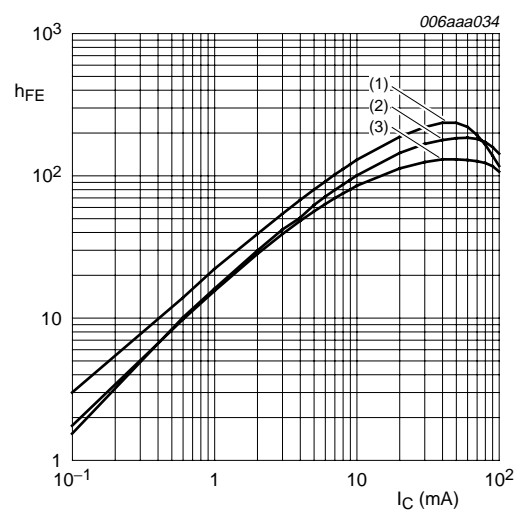


Fig 7. TR2: DC current gain as a function of collector current; typical values

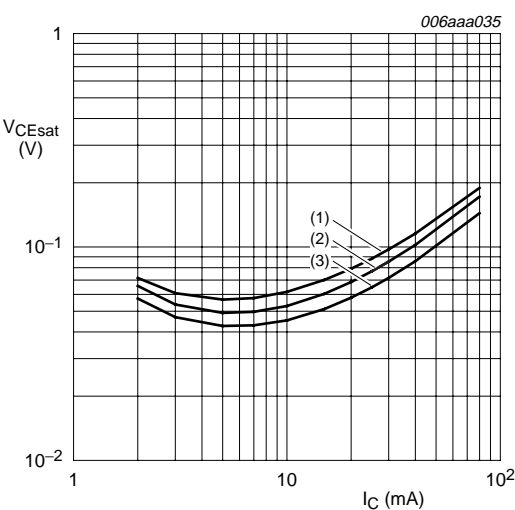


Fig 8. TR2: Collector-emitter saturation voltage as a function of collector current; typical values

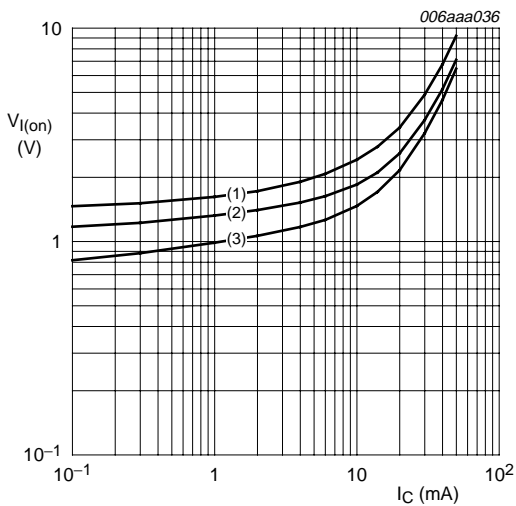


Fig 9. TR2: On-state input voltage as a function of collector current; typical values

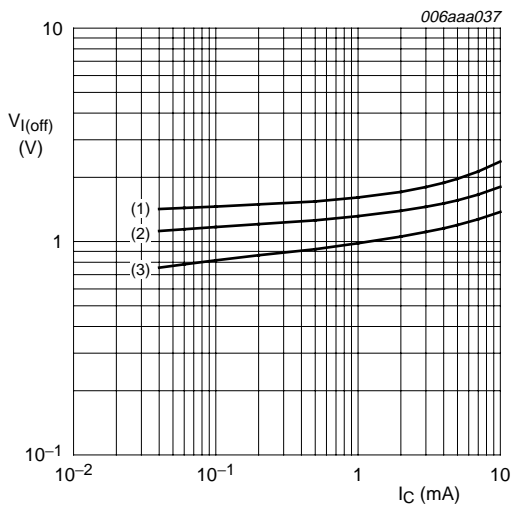


Fig 10. TR2: Off-state input voltage as a function of collector current; typical values

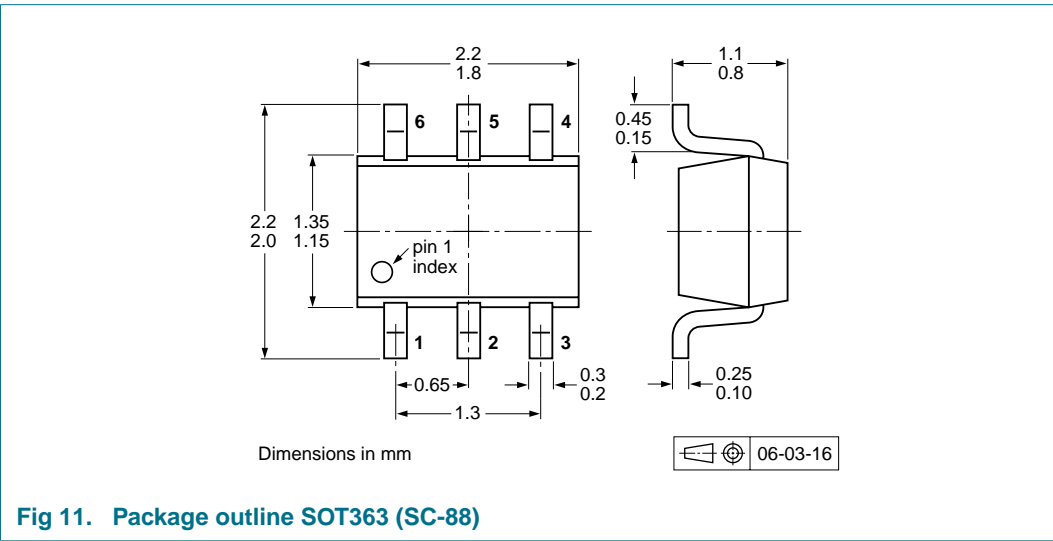


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



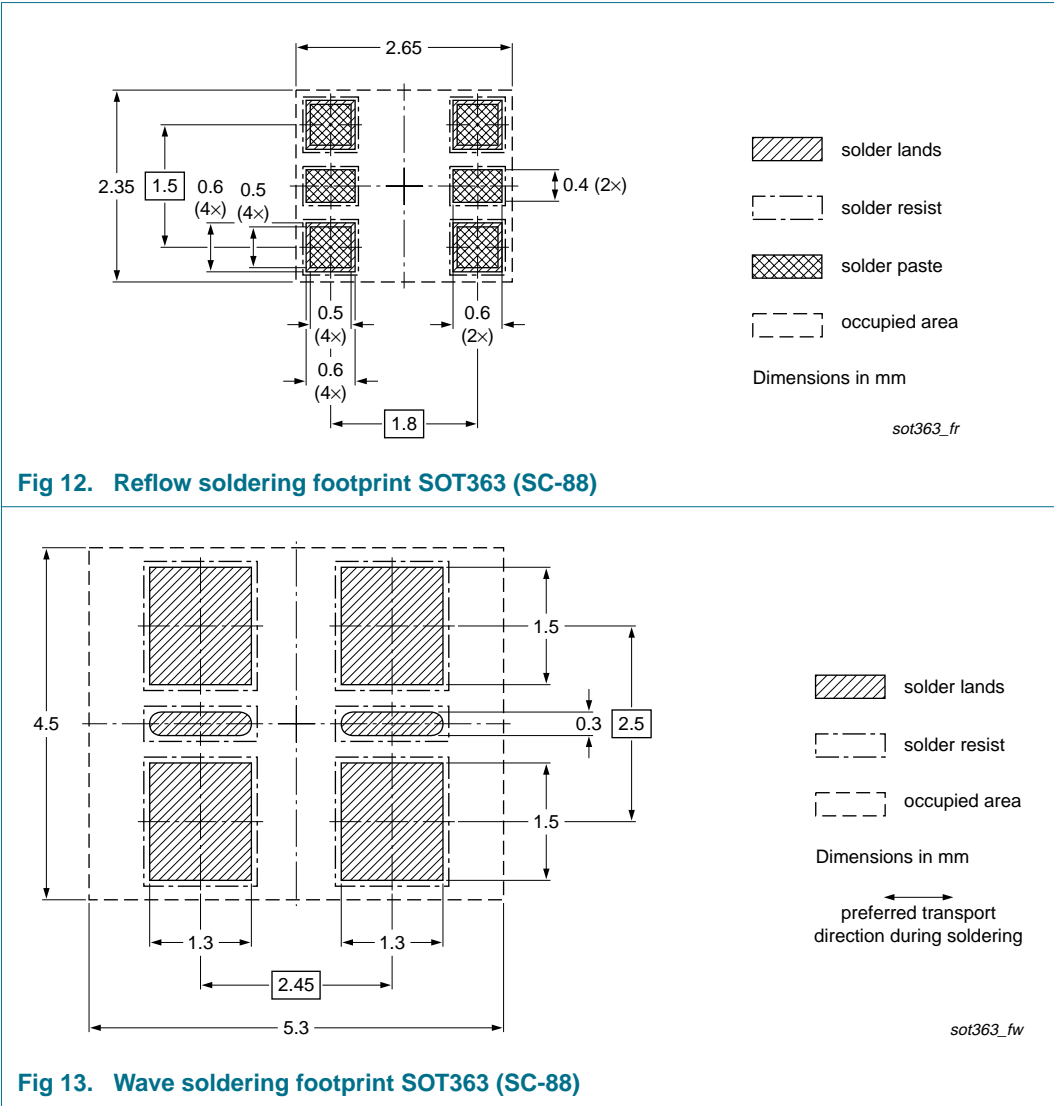
10. Packing information

**Table 8. Packing methods**  
The indicated -xxx are the last three digits of the 12NC ordering code.<sup>[1]</sup>

Type number	Package	Description	Packing quantity	
			3000	10000
PUML1/DG	SOT363	4 mm pitch, 8 mm tape and reel; T1	<sup>[2]</sup> -115	-135
		4 mm pitch, 8 mm tape and reel; T2	<sup>[3]</sup> -125	-165

[1] For further information and the availability of packing methods, see [Section 14](#).  
[2] T1: normal taping  
[3] T2: reverse taping

11. Soldering



12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PUML1_DG_1	20080714	Product data sheet	-	-

## 13. Legal information

### 13.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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